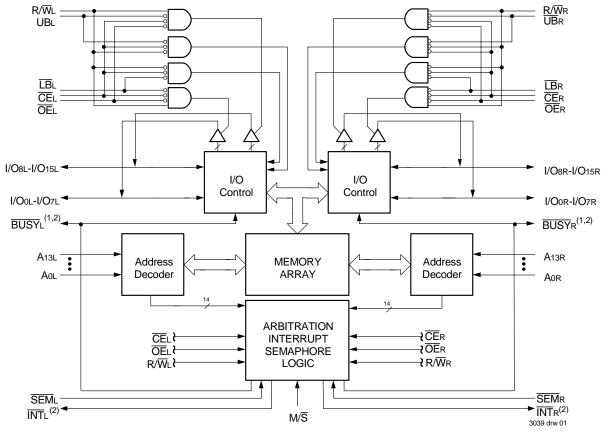
	DUAL-PORT RAM WITH INTERRUPT	<b>IDT70261S/L</b> E 15, 2018
<ul> <li>Features</li> <li>True Dual-Ported memory cells which allow simultaneous access of the same memory location</li> <li>High-speed access <ul> <li>Commercial: 15/20/25/35/55ns (max.)</li> <li>Industrial 20/25ns (max.)</li> </ul> </li> <li>Low-power operation <ul> <li>IDT70261S</li> <li>Active: 750mW (typ.)</li> <li>Standby: 5mW (typ.)</li> <li>Standby: 1mW (typ.)</li> </ul> </li> </ul>	<ul> <li>IDT70261 easily expands data bus wi using the Master/Slave select when one device</li> <li>M/S = H for BUSY output flag on Mas M/S = L for BUSY input on Slave</li> <li>Busy and Interrupt Flags</li> <li>On-chip port arbitration logic</li> <li>Full on-chip hardware support of se between ports</li> <li>Fully asynchronous operation from</li> <li>TTL-compatible, single 5V (±10%) pc</li> <li>Available in 100-pin Thin Quad Flatp</li> <li>Industrial temperature range (-40°C</li> </ul>	cascading more than ster, maphore signaling either port wer supply ack

- Separate upper-byte and lower-byte control for multiplexed ٠ bus compatibility
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- ٠ Green parts available. See ordering information



### NOTES:

- 1. (MASTER):  $\overline{\text{BUSY}}$  is output; (SLAVE):  $\overline{\text{BUSY}}$  is input.
- 2. BUSY and INT outputs are non-tri-stated push-pull.

**JUNE 2018** 

## Functional Block Diagram

### IDT70261S/L High-Speed 16K x 16 Dual-Port Static RAM with Interrupt

### Industrial and Commercial Temperature Ranges

### Description

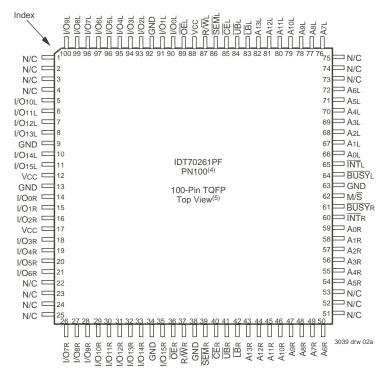
The IDT70261 is a high-speed 16K x 16 Dual-Port Static RAM. The IDT70261 is designed to be used as a stand-alone Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 32-bit-or-more word systems. Using the IDTMASTER/SLAVE Dual-Port RAM approach in 32-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

This device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by  $\overline{CE}$  permits the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using CMOS high-performance technology, these devices typically operate on only 750mW of power.

The IDT70261 is packaged in a 100-pin TQFP.

## PinConfigurations<sup>(1,2,3)</sup>



### NOTES:

- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

### **Pin Names**

Left Port	Right Port	Names
Ē	ĒĒR	Chip Enable
R/₩L	R/Wr	Read/Write Enable
ŌĒL	<del>0E</del> r	Output Enable
Aol - A13l	Aor - A13r	Address
I/Ool - I/O15L	I/O0r - I/O15r	Data Input/Output
SEML	<b>SEM</b> R	Semaphore Enable
ŪBL	ŪBR	Upper Byte Select
LBL	<b>LB</b> R	Lower Byte Select
ĪNT∟	ĪNTR	Interrupt Flag
BUSYL	<b>BUSY</b> R	Busy Flag
N	/ <del>S</del>	Master or Slave Select
V	CC	Power
G	ND	Ground

## Maximum Operating Temperature and Supply Voltage $^{\scriptscriptstyle (1,2)}$

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

1. This is the parameter TA. This is the "instant on"case temperature.

## Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2		6.0 <sup>(2)</sup>	V
VIL	Input Low Voltage	-0.5 <sup>(1)</sup>		0.8	V

NOTES:

3039 tbl 02

3039 tbl 03

1. VIL  $\geq$  -1.5V for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

## Truth Table I - Non-Contention Read/Write Control

		Inpu	uts <sup>(1)</sup>			Out	puts	
ĈĒ	R/₩	ŌĒ	UB	LB	SEM	I/O8-15	I/O0-7	Mode
Н	Х	Х	Х	Х	Н	High-Z	High-Z	Deselected: Power-Down
Х	Х	Х	Н	Н	Η	High-Z	High-Z	Both Bytes Deselected
L	L	Х	L	Н	Η	DATAIN	High-Z	Write to Upper Byte Only
L	L	Х	Н	L	Η	High-Z	DATAIN	Write to Lower Byte Only
L	L	Х	L	L	Η	DATAIN	DATAIN	Write to Both Bytes
L	Н	L	L	Н	Η	DATAOUT	High-Z	Read Upper Byte Only
L	Н	L	Н	L	Η	High-Z	DATAOUT	Read Lower Byte Only
L	Н	L	L	L	Η	DATAOUT	DATAOUT	Read Both Bytes
Х	Х	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled

NOTE:

1. AOL — A13L  $\neq$  AOR — A13R.

## Truth Table II – Semaphore Read/Write Control<sup>(1)</sup>

		Inp	uts			Out	puts	
Ē	R/₩	ŌĒ	ŪB	LB	SEM	<b>I/O</b> 8-15	I/O0-7	Mode
Н	Н	L	Х	Х	L	DATAOUT	DATAOUT	Read Data in Semaphore Flag
Х	Н	L	Н	Н	L	DATAOUT	DATAOUT	Read Data in Semaphore Flag
Н	$\uparrow$	Х	Х	Х	L	DATAIN	DATAIN	Write I/Oo into Semaphore Flag
Х	$\uparrow$	Х	Н	Н	L	DATAIN	DATAIN	Write I/Oo into Semaphore Flag
L	Х	Х	L	Х	L			Not Allowed
L	Х	Х	Х	L	L			Not Allowed

### NOTE:

1. There are eight semaphore flags written to via I/Oo and read from all I/O's(I/Oo - I/O15). These eight semaphores are addressed by Ao - A2.

3039 tbl 05

3039 tbl 04

3039 tbl 07

## Absolute Maximum Ratings<sup>(1)</sup>

Symbol	Rating	Commercial & Industrial	Unit
Vterm <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
lout	DC Output Current	50	mA
			3039 tbl 06

### NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to  $\leq~$  20mA for the period of VTERM  $~\geq~$  Vcc + 10%.

## Capacitance<sup>(1)</sup> (TA = +25°C, f = 1.0Mhz)

Symbol	Parameter	Conditions <sup>(2)</sup>	Мах.	Unit
Cin	Input Capacitance	VIN = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF

NOTES:

1. This parameter is determined by device characterization but is not production tested.

 3dV represents the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ( $Vcc = 5.0V \pm 10\%$ )

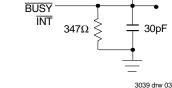
			70261S		702		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Мах.	Unit
Lu	Input Leakage Current <sup>(1)</sup>	Vcc = 5.5V, VIN = 0V to Vcc	—	10	_	5	μA
Ilo	Output Leakage Current	$\overline{CE}$ = VIH, VOUT = 0V to VCC	_	10	_	5	μA
Vol	Output Low Voltage	Iol = 4mA	—	0.4	_	0.4	V
Vон	Output High Voltage	Iон = -4mA	2.4	—	2.4	_	V

### NOTE:

1. At Vcc < 2.0V, input leakages are undefined.

## AC Test Conditions

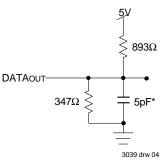
Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2
	30.39 tbl 09



DATAOUT

<u>5</u>V

893Ω



3039 tbl 08

Figure 1. AC Output Test Load

Figure 2. Output Test Load (for tLz, tHz, twz, tow) \*Including scope and jig.

# DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1)</sup> ( $Vcc = 5.0V \pm 10\%$ )

					7026 Com'l		7026 Com'l		7026 Com'l		
Symbol	Parameter	Test Condition	Versi	on	Тур. <sup>(2)</sup>	Max.	Тур. <sup>(2)</sup>	Max.	Typ. <sup>(2)</sup>	Max.	Unit
ICC	Dynamic Operating Current (Both Ports Active)	$\frac{\overline{\text{CE}} = \text{VIL, Outputs Disabled}}{\text{SEM} = \text{VIH}}{\text{f} = \text{fMAX}^{(S)}} \frac{\text{COM'L}}{\text{IND}} \frac{\text{S}}{\text{L}}$	190 190	325 285	180 180	315 275	170 170	305 265	mA		
			IND				 180	 315	170 —	345 —	
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\label{eq:cell} \begin{array}{l} \overline{CE}_L = \overline{CE}_R = VH \\ \overline{SEM}_R = \overline{SEM}_L = VH \\ f = fMAX^{(3)} \end{array}$	COM'L	S L	35 35	95 70	30 30	85 60	25 25	85 60	mA
	inputs)		IND	S L			30	80	25 —	100	
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}^{*}A^{*} = VIL \text{ and } \overline{CE}^{*}B^{*} = VIH^{(5)}$ Active Port Outputs Disabled, $f=fMaX^{(3)}$	COM'L	S L	125 125	220 190	115 115	210 180	105 105	200 170	mA
		<u>SEM</u> R = <u>SEM</u> L = V⊪	IND	S L			 115	 210	105 —	230	
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports $\overline{CEL}$ and $\overline{CER} \ge VCC - 0.2V$ $VIN \ge VCC - 0.2V_{or}$	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 5	mA
	inputs)	$\frac{V_{IN} \le 0.2V, f = 0^{(4)}}{SEMR} = \frac{SEML}{SEML} \ge VCC - 0.2V$	IND	S L			0.2	10	1.0	30	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\overline{CE}$ "A" < 0.2V and	COM'L	S L	120 120	195 170	110 110	185 160	100 100	170 145	mA
	inputs)	SETVICE = SETVICE = $0.2V$ $VIN \ge VCC = 0.2V$ or $VIN \le 0.2V$ Active Port Outputs Disabled $f = fMax^{(3)}$	IND	S L			— 110	 185	100 —	200	

						1X35 Only	70261X55 Com'l Only		
Symbol	Parameter	Test Condition	Versi	ion	Тур. <sup>(2)</sup>	Max.	Тур. <sup>(2)</sup>	Max.	Un
ICC	Dynamic Operating Current (Both Ports Active)	$\overline{\underline{CE}} = V\mathbb{I}$ , Outputs Disabled SEM = VIH f = fMAX <sup>(3)</sup>	COM'L	S L	160 160	295 255	150 150	270 230	m/
	(Both Polis Active)	I = IMAX*'	IND	S L					m/
ISB1	Standby Current (Both Ports - TTL Level	$\label{eq:cell} \begin{split} \overline{CEL} &= \overline{CER} = VIH\\ \overline{SEMR} &= \overline{SEML} = VIH\\ f &= fMAX^{(3)} \end{split}$	COM'L	S L	20 20	85 60	13 13	85 60	m
	Inputs) $f = fMAX^{(3)}$	r = max <sup>ey</sup>	IND	S L					m
ISB2	Standby Current (One Port - TTL Level $\overline{CE}^*A^* = VIL$ and $\overline{CE}^*B^* = VIH^{(5)}$ Active Port Outputs Disabled,	Active Port Outputs Disabled.	COM'L	S L	95 95	185 155	85 85	165 135	m
	Inputs)	$\frac{f=fMAX^{(3)}}{SEMR} = \frac{1}{SEML} = VIH$	IND	S L					m
ISB3	Full Standby Current (Both Ports - All CMOS	Both Ports $\overline{CE}_{L}$ and $\overline{CE}_{R} \ge VCC - 0.2V$	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	m
	Level Inputs)	$ \begin{array}{l} \mbox{VIN} \geq \mbox{Vcc} & - \ 0.2 \mbox{V or} \\ \mbox{VIN} \leq \ 0.2 \mbox{V}, \ f = \ 0^{(4)} \\ \mbox{SEMR} = \ \mbox{SEML} \geq \mbox{Vcc} & - \ 0.2 \mbox{V} \\ \end{array} $	IND	S L					m
ISB4	$\begin{array}{l} \mbox{(One Port - All CMOS} \\ \mbox{Level Inputs)} \end{array} \qquad $	COM'L	S L	90 90	160 135	80 80	135 110	m	
		VIN <u>&gt;</u> VCC - 0.2V or VIN <u>&lt;</u> 0.2V	IND	S L					m

NOTES:

'X' in part numbers indicates power rating (S or L).
 Vcc = 5V, TA = +25°C, and are not production tested. Icccc = 120mA (Typ.)
 At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/tRc, and using "AC Test Conditions" of input levels of GND to 3V.

4. f = 0 means no address or control lines change.

5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(4)</sup>

			70261X15 Com'l Only				1X25 & Ind	
Symbol	Parameter Min. Max.		Min.	Max.	Min.	Max.	Unit	
READ CYCLE	•	•				•		
trc	Read Cycle Time	15		20	—	25		ns
taa	Address Access Time		15		20		25	ns
tace	Chip Enable Access Time <sup>(3)</sup>		15		20		25	ns
tabe	Byte Enable Access Time <sup>(3)</sup>		15		20		25	ns
taoe	Output Enable Access Time		10		12		13	ns
toн	Output Hold from Address Change	3		3		3		ns
tLZ	Output Low-Z Time <sup>(1,2)</sup>	3		3	_	3		ns
tHZ	Output High-Z Time <sup>(1,2)</sup>		10		12		15	ns
tPU	Chip Enable to Power Up Time <sup>(2)</sup>	0		0	—	0		ns
tPD	Chip Disable to Power Down Time <sup>(2)</sup>		15		20		25	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	10		10	—	12		ns
tsaa	Semaphore Address Access Time		15		20		25	ns

3039 tbl 12a

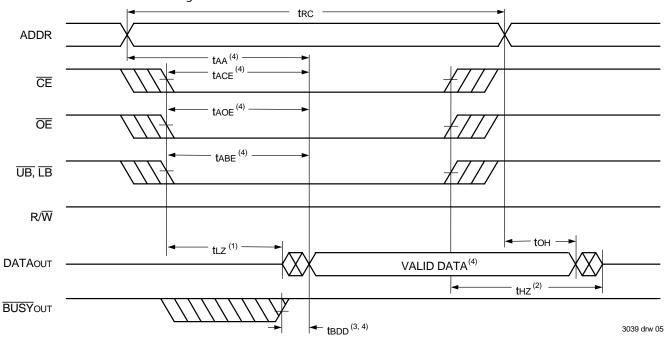
			1X35 I Only	70261X55 Com'l Only			
Symbol	Parameter	Min. Max.		Min.	Max.	Unit	
READ CYCLE							
tRC	Read Cycle Time	35		55	_	ns	
taa	Address Access Time		35		55	ns	
tace	Chip Enable Access Time <sup>(3)</sup>		35		55	ns	
<b>t</b> ABE	Byte Enable Access Time <sup>(3)</sup>		35		55	ns	
taoe	Output Enable Access Time		20		30	ns	
toн	Output Hold from Address Change	3		3		ns	
tLZ	Output Low-Z Time <sup>(1,2)</sup>	3		3		ns	
tHZ	Output High-Z Time <sup>(1,2)</sup>		15		25	ns	
tpu	Chip Enable to Power Up Time <sup>(2)</sup>	0		0		ns	
tpd	Chip Disable to Power Down Time <sup>(2)</sup>		35		50	ns	
tsop	Semaphore Flag Update Pulse (OE or SEM)	15		15		ns	
tsaa	Semaphore Address Access Time		35		55	ns	
	-	•	-	-		3039 tbl 12b	

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested. 3. To access RAM,  $\overline{CE} = V_{IL}$  and  $\overline{SEM} = V_{IH}$ . To access semaphore,  $\overline{CE} = V_{IH}$  and  $\overline{SEM} = V_{IL}$ . 4. 'X' in part numbers indicates power rating (S or L).

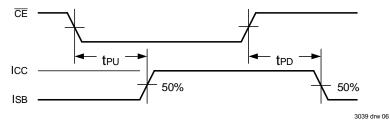
Waveform of Read Cycles<sup>(5)</sup>



### NOTES:

- 1. Timing depends on which signal is asserted last,  $\overline{OE}$ ,  $\overline{CE}$ ,  $\overline{LB}$ , or  $\overline{UB}$ .
- 2. Timing depends on which signal is de-asserted first  $\overline{CE}$ ,  $\overline{OE}$ ,  $\overline{LB}$ , or  $\overline{UB}$ .
- 3. tbbb delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA or tBDD.
- 5.  $\overline{SEM} = VIH.$

## Timing of Power-Up Power-Down



### AC Electrical Characteristics Over the Operating Temperature and Supply Voltage<sup>(5)</sup>

		7020 Com	51X15 I Only	702 Com	61X20 I & Ind	70261X25 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CY	CLE							
twc	Write Cycle Time	15		20		25		ns
tew	Chip Enable to End-of-Write <sup>(3)</sup>	12		15		20		ns
taw	Address Valid to End-of-Write	12		15		20		ns
tas	Address Set-up Time <sup>(3)</sup>	0	_	0		0	_	ns
twp	Write Pulse Width	12		15		20		ns
twr	Write Recovery Time	0		0		0		ns
tow	Data Valid to End-of-Write	10		15		15		ns
tHZ	Output High-Z Time <sup>(1,2)</sup>	_	10		12		15	ns
tDH	Data Hold Time <sup>(4)</sup>	0		0		0		ns
twz	Write Enable to Output in High-Z <sup>(1,2)</sup>	_	10		12		15	ns
tow	Output Active from End-of-Write <sup>(1,2,4)</sup>	0		0		0		ns
tswrd	SEM Flag Write to Read Time	5	_	5		5	_	ns
tsps	SEM Flag Contention Window	5	—	5		5		ns
	1		-			-	3	039 tbl 13a
							1X55 I Only	
Symbol	Parameter				Max.	Min.	Max.	Unit
WRITE CY	CLE							
twc	Write Cycle Time			35		55		ns
tew	Chip Enable to End-of-Write <sup>(3)</sup>			30		45	_	ns
taw	Address Valid to End-of-Write			30		45		ns

IVVC	whe cycle nine	30		55
tew	Chip Enable to End-of-Write <sup>(3)</sup>	30		45
taw	Address Valid to End-of-Write	30		45
tas	Address Set-up Time <sup>(3)</sup>	0		0
twp	Write Pulse Width	25		40
twr	Write Recovery Time	0		0
tow	Data Valid to End-of-Write	15		30
tнz	Output High-Z Time <sup>(1,2)</sup>		15	_
tdн	Data Hold Time <sup>(4)</sup>	0		0
twz	Write Enable to Output in High-Z <sup>(1,2)</sup>		15	
tow	Output Active from End-of-Write <sup>(1,2,4)</sup>	0		0
tswrd	SEM Flag Write to Read Time	5		5
tsps	SEM Flag Contention Window	5		5

3039 tbl 13b

ns

25

\_\_\_\_

25

\_\_\_\_

\_\_\_\_

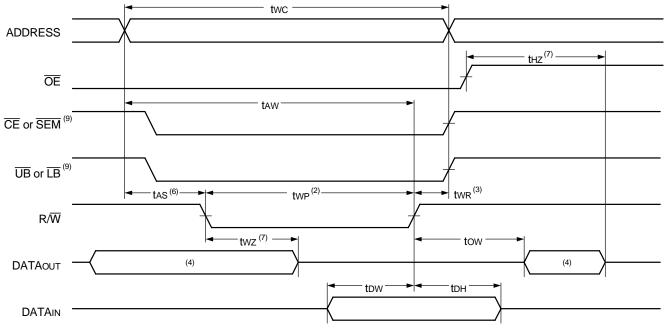
1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

This parameter is guaranteed by device characterization, but is not production tested. 2.

3. To access RAM,  $\overrightarrow{CE} = V_{IL}$  and  $\overrightarrow{SEM} = V_{IH}$ . To access semaphore,  $\overrightarrow{CE} = V_{IH}$  and  $\overrightarrow{SEM} = V_{IL}$ . Either condition must be valid for the entire tew time. 4. The specification for tbH must be met by the device supplying write data to the RAM under all operating conditions. Although tbH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

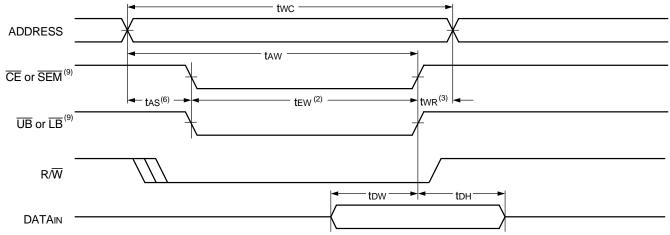
5. 'X' in part numbers indicates power rating (S or L).

## Timing Waveform of Write Cycle No. 1, R/W Controlled Timing<sup>(1,5,8)</sup>



3039 drw 07

## Timing Waveform of Write Cycle No. 2, **CE**, **UB**, **LB** Controlled Timing<sup>(1,5)</sup>

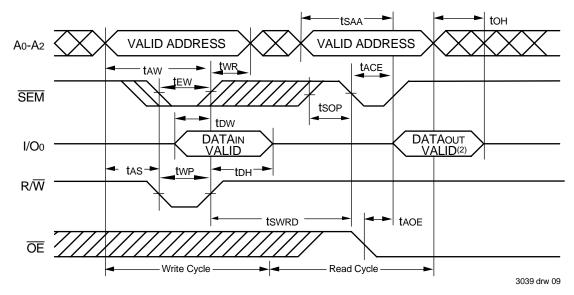


3039 drw 08

### NOTES:

- 1.  $R/\overline{W}$  or  $\overline{CE}$  or  $\overline{UB}$  and  $\overline{LB}$  = VIH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a CE = VIL and a R/W = VIL for memory array writing cycle.
- 3. two is measured from the earlier of  $\overline{CE}$  or  $\overline{R/W}$  (or  $\overline{SEM}$  or  $\overline{R/W}$ ) going VIH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM = VIL transition occurs simultaneously with or after the RIW = VIL transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last,  $\overline{CE}$  or  $R/\overline{W}$ .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If  $\overline{OE} = V_{IL}$  during RW controlled write cycle, the write pulse width must be the larger of twp or (twz + tbw) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If  $\overline{OE} = V_{IH}$  during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM,  $\overline{CE} = V_{IL}$  and  $\overline{SEM} = V_{IH}$ . To access semaphore,  $\overline{CE} = V_{IH}$  and  $\overline{SEM} = V_{IL}$ . tew must be met for either condition.

Timing Waveform of Semaphore Read after Write Timing, Either Side<sup>(1)</sup>

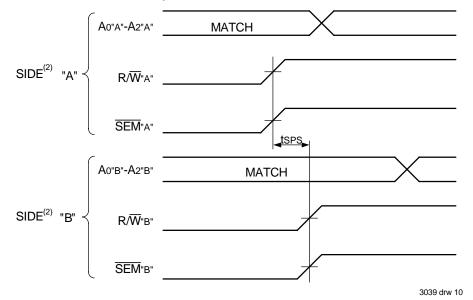


### NOTES:

1.  $\overline{CE} = V_{IH}$  or  $\overline{UB}$  and  $\overline{LB} = V_{IH}$  for the duration of the above timing (both write and read cycle).

2. "DATAOUT VALID" represents all I/O's (I/Oo-I/O15) equal to the semaphore value.

## Timing Waveform of Semaphore Write Contention<sup>(1,3,4)</sup>



NOTES:

- 1. Dor = Dol = VIL,  $\overline{CE}R = \overline{CE}L = VIH$ , or both  $\overline{UB} \& \overline{LB} = VIH$ .
- 2. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 3. This parameter is measured from RIW"A" or SEM"A" going HIGH to RIW"B" or SEM"B" going HIGH.
- 4. If tsps is not satisfied, there is no guarantee which side will be granted the semaphore flag.

3039 tbl 14b

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(6,7)</sup>

			1X15 I Only		1X20 & Ind	70261X25 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY TIMING	б (M/S=VIн)							-
tbaa	BUSY Access Time from Address Match		15		20		20	ns
tbda	BUSY Disable Time from Address Not Matched		15		20		20	ns
tBAC	BUSY Access Time from Chip Enable Low		15		20		20	ns
tBDC	BUSY Access Time from Chip Enable High		15		17	_	17	ns
taps	Arbitration Priority Set-up Time <sup>(2)</sup>	5		5		5		ns
tBDD	BUSY Disable to Valid Data <sup>(3)</sup>		18		30	_	30	ns
twн	Write Hold After BUSY <sup>(5)</sup>	12		15		17		ns
BUSY TIMING	(M/S=VIL)							
twв	BUSY Input to Write <sup>(4)</sup>	0		0		0		ns
twн	Write Hold After BUSY <sup>(5)</sup>	12		15	_	17		ns
PORT-TO-POR	RT DELAY TIMING							
twdd	Write Pulse to Data Delay <sup>(1)</sup>		30		45		50	ns
tddd	Write Data Valid to Read Data Delay <sup>(1)</sup>		25		30		35	ns
	•	•		•	•	•	•	3039 tbl 14a

70261X35 70261X55 Com'l Only Com'l Only Unit Symbol Parameter Min. Max. Min. Max. BUSY TIMING (M/S=VIH) tBAA **BUSY** Access Time from Address Match 20 45 \_\_\_\_\_ ns 20 40 **t**BDA BUSY Disable Time from Address Not Matched ns \_\_\_\_\_ 20 **BUSY** Access Time from Chip Enable Low 40 **t**BAC \_ ns **t**BDC **BUSY** Access Time from Chip Enable High 20 35 ns \_\_\_\_ Arbitration Priority Set-up Time<sup>(2)</sup> 5 **t**APS 5 \_\_\_\_ ns **BUSY** Disable to Valid Data<sup>(3)</sup> 35 40 **t**BDD ns \_\_\_\_\_ Write Hold After BUSY<sup>(5)</sup> twн 25 \_\_\_\_\_ 25 \_\_\_\_ ns BUSY TIMING (M/S=VIL) **BUSY** Input to Write<sup>(4)</sup> 0 twв 0 ns Write Hold After BUSY<sup>(5)</sup> 25 25 twн ns PORT-TO-PORT DELAY TIMING twdd Write Pulse to Data Delay<sup>(1)</sup> 60 80 ns \_ Write Data Valid to Read Data Delay<sup>(1)</sup> 45 65 todd ns

NOTES:

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Wave form of Write with Port-to-Port Read and BUSY (M/S = VI+)".

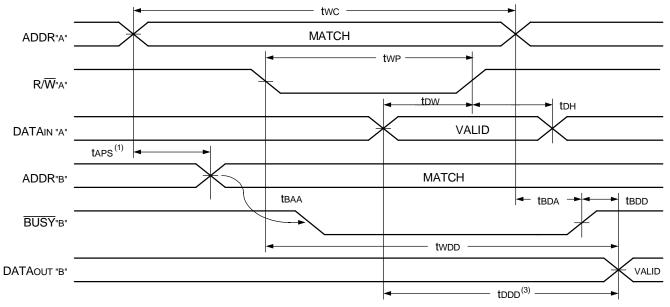
2. To ensure that the earlier of the two ports wins.

- 4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".
- 5. To ensure that a write cycle is completed on port "B" after contention on port "A".
- 6. 'X' in part numbers indicates power rating (S or L).

<sup>3.</sup> tBDD is a calculated parameter and is the greater of 0, twDD - twp (actual), or tDDD - tDw (actual).

3039 drw 11

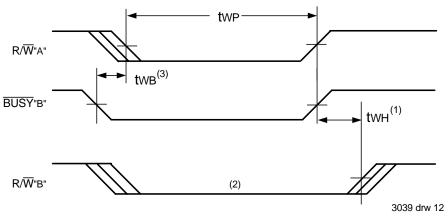
## Timing Waveform of Write with Port-to-Port Read and $\overline{\text{BUSY}}$ (M/ $\overline{\text{S}}$ = VIH)<sup>(2,4,5)</sup>



NOTES:

- 1. To ensure that the earlier of the two ports wins. taps is ignored for  $M/\overline{S} = VIL$  (SLAVE).
- $2. \quad \overline{CE}_L = \overline{CE}_R = VIL.$
- 3.  $\overline{OE} = VIL$  for the reading port.
- 4. If M/S = VIL (slave), BUSY is an input. Then for this example BUSY A\* = VIH and BUSY B\* input is shown above.
- 5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

## Timing Waveform of Write with $\overline{\text{BUSY}}$ (M/ $\overline{\text{S}}$ = VIL)

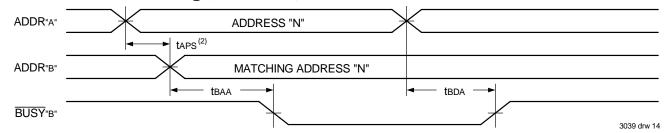


NOTES:

- 1. twH must be met for both  $\overline{\text{BUSY}}$  input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. twb is only for the "SLAVE" version.

High-Speed 10	6K x 16 Dual-Port Static RAM with Interrupt	Industrial and Commercial Temperature Ranges
Wavefori	m of <b>BUSY</b> Arbitration Controlled	by <b>CE</b> Timing (М/ <b>S</b> = VIH) <sup>(1)</sup>
ADDR"A" and "B"	ADDRESSES N	ЛАТСН
- CE <sup>"</sup> A"		
— СЕ <sub>"В"</sub>		
BUSY"B"		▲ tBDC ▲ 3039 drw 13

## Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing (M/ $\mathbf{S}$ = VIH)<sup>(1)</sup>



### NOTES:

IDT70261S/L

- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
- 2. If tAPS is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1)</sup>

			1X15 I Only	70261X20 Com'l & Ind		70261X25 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
INTERRUPT 1	riming		-			-		
tas	Address Set-up Time	0		0		0		ns
twR	Write Recovery Time	0		0		0		ns
ti∾s	Interrupt Set Time		15		20		20	ns
tinr	Interrupt Reset Time		15		20		20	ns

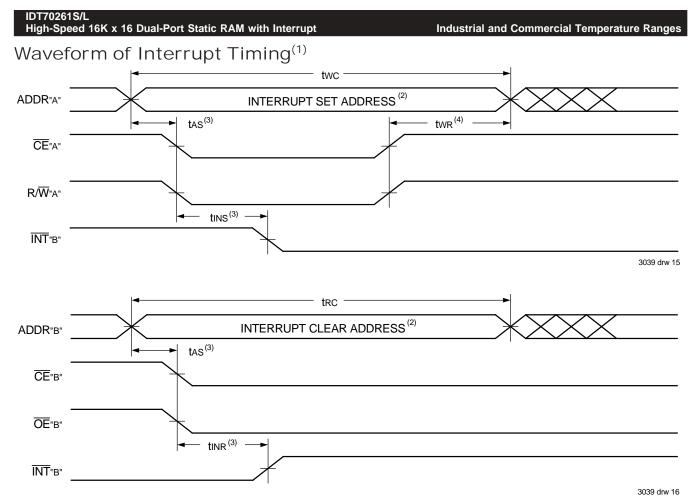
3039 tbl 15a

3039 tbl 15b

			70261X35 Com'l Only		70261X55 Com'l Only	
Symbol	Parameter	Max.	Min.	Max.	Unit	
INTERRUPT T	IMING					
tas	Address Set-up Time	0		0		ns
twR	Write Recovery Time	0		0		ns
tins	Interrupt Set Time		25		40	ns
tinr	Interrupt Reset Time		25		40	ns

### NOTES:

1. 'X' in part numbers indicates power rating (S or L).



### NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. See Interrupt Truth Table.

- 3. Timing depends on which enable signal ( $\overline{CE}$  or  $R/\overline{W}$ ) is asserted last.
- 4. Timing depends on which enable signal (CE or R/W) is de-asserted first.

## **Truth** Tables

Left Port						Right Po	t			
R/₩L	CEL		A13L-A0L	ĪNTL	R/WR	ĊĒr	<b>OE</b> R	A13R-A0R	ĪNTR	Function
L	L	Х	3FFF	Х	Х	Х	Х	Х	L <sup>(2)</sup>	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	3FFF	H <sup>(3)</sup>	Reset Right INTR Flag
Х	Х	Х	Х	L <sup>(3)</sup>	L	L	Х	3FFE	Х	Set Left INTL Flag
Х	L	L	3FFE	H <sup>(2)</sup>	Х	Х	Х	Х	Х	Reset Left INTL Flag

## Truth Table III — Interrupt Flag<sup>(1)</sup>

### NOTES:

1. Assumes  $\overline{\text{BUSY}}_{L} = \overline{\text{BUSY}}_{R} = V_{IH}$ .

2. If  $\overline{\text{BUSY}}L = VIL$ , then no change.

3. If  $\overline{\text{BUSY}}_{R} = \text{VIL}$ , then no change.

3039 tbl 16

## Truth Table IV — Address **BUSY** Arbitration

	Inputs			puts	
Ē	ĊĒr	Aol-A13l Aor-A13r	BUS YL <sup>(1)</sup>	BUSYR <sup>(1)</sup>	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit <sup>(3)</sup>

### NOTES:

3039 tbl 17

1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT70261 are push-pull, not open drain outputs. On slaves the BUSY input internally inhibits writes.

"L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.

3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

## Truth Table V — Example of Semaphore Procurement Sequence<sup>(1,2,3)</sup>

Functions	D0 - D15 Left	Do - D15 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

### NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT70261.

2. There are eight semaphore flags written to via 1/00 and read from all 1/0's (1/00-1/015). These eight semaphores are addressed by Ao - A2.

3.  $\overline{CE} = V_{IH}$ ,  $\overline{SEM} = V_{IL}$  to access the semaphores. Refer to the Semaphore Read/Write Control Truth Table.

## Functional Description

The IDT70261 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70261 has an automatic power down feature controlled by  $\overline{CE}$ . The  $\overline{CE}$  controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ( $\overline{CE} = VIH$ ). When a port is enabled, access to the entire memory array is permitted.

### Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag

 $(\overline{INT}L)$  is asserted when the right port writes to memory location 3FFE (HEX), where a write is defined as  $\overline{CE}R = R/\overline{W}R = VIL$  per Truth Table III. The left port clears the interrupt through access of address location 3FFE when  $\overline{CE}L = \overline{OE}L = VIL$ ,  $R/\overline{W}$  is a "don't care". Likewise, the right port interrupt flag ( $\overline{INT}R$ ) is asserted when the left port writes to memory location 3FFF (HEX) and to clear the interrupt flag ( $\overline{INT}R$ ), the right port must read the memory location 3FFF. The message (16 bits) at 3FFE or 3FFF is user-defined since it is an addressable SRAM location. If the interrupt function is not used, address locations 3FFE and 3FFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table III for the interrupt operation.

3039 tbl 18

#### IDT70261S/L High-Speed 16K x 16 Dual-Port Static RAM with Interrupt

### **BusyLogic**

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The  $\overline{\text{BUSY}}$  pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a  $\overline{\text{BUSY}}$  indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of BUSY logic is not desirable, the BUSY logic can be disabled by placing the part in slave mode with the M/S pin. Once in slave mode the BUSY pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the BUSY pins high. If desired, unintended write operations can be prevented to a port by tying the BUSY pin for that port low.

The BUSY outputs on the IDT 70261 RAM in master mode, are pushpull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

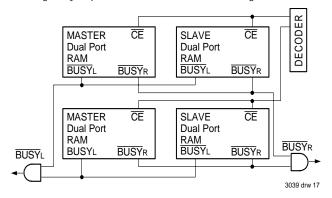


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70261 RAMs.

## Width Expansion with Busy Logic Master/Salve Arrays

When expanding an IDT70261 RAM array in width while using  $\overline{BUSY}$  logic, one master part is used to decide which side of the RAM array will receive a  $\overline{BUSY}$  indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the  $\overline{BUSY}$  signal as a write inhibit signal. Thus on the IDT70261 RAM the  $\overline{BUSY}$  pin is an output if the part is used as a master (M/ $\overline{S}$  pin = VIH), and the  $\overline{BUSY}$  pin is an input if the part used as a slave (M/ $\overline{S}$  pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the array and another master indicating BUSY on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write

pulse can be initiated with either the  $R/\overline{W}$  signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

## Semaphores

The IDT70261 is an extremely fast Dual-Port 16K x 16 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from, orwritten to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by  $\overrightarrow{CE}$ , the Dual-Port RAM enable, and  $\overrightarrow{SEM}$ , the semaphore enable. The  $\overrightarrow{CE}$  and  $\overrightarrow{SEM}$  pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table V where  $\overrightarrow{CE}$  and  $\overrightarrow{SEM}$  are both HIGH.

Systems which can best use the IDT70261 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70261's hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70261 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very highspeed systems.

### How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request

### IDT70261S/L <u>High-Speed 16K x 16</u> Dual-Port Static RAM with Interrupt

### Industrial and Commercial Temperature Ranges

that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active low. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

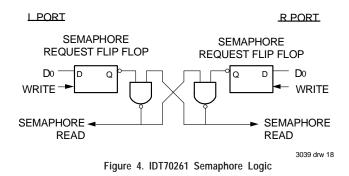
The eight semaphore flags reside within the IDT70261 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a low input on the  $\overline{SEM}$  pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address,  $\overline{OE}$ , and  $R/\overline{W}$ ) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Table V). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able towrite a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (SEM) and output enable ( $\overline{OE}$ ) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (SEM or  $\overline{OE}$ ) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table V). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip



over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay low until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

### Using Semaphores—Some Examples

Perhaps the simplest application of semaphores is their application as resource markers for the IDT70261's Dual-Port RAM. Say the 16K x 16 RAM was to be divided into two 8K x 16 blocks which were to be dedicated at any one time to servicing either the left or right port. Semaphore 0 could be used to indicate the side which would control the lower section of memory, and Semaphore 1 could be defined as the indicator for the upper section of memory.

To take a resource, in this example the lower 8K of Dual-Port RAM, the processor on the left port could write and then read a zero in to Semaphore 0. If this task were successfully completed (a zero was read back rather than a one), the left processor would assume control of the lower 8K. Meanwhile the right processor was attempting to gain control

### IDT70261S/L High-Speed 16K x 16 Dual-Port Static RAM with Interrupt

### Industrial and Commercial Temperature Ranges

of the resource after the left processor, it would read back a one in response to the zero it had attempted to write into Semaphore 0. At this point, the software could choose to try and gain control of the second 8K section by writing, then reading a zero into Semaphore 1. If it succeeded in gaining control, it would lock out the left side.

Once the left side was finished with its task, it would write a one to Semaphore 0 and may then try to gain access to Semaphore 1. If Semaphore 1 was still occupied by the right side, the left side could undo its semaphore request and perform other tasks until it was able to write, then read a zero into Semaphore 1. If the right processor performs a similar task with Semaphore 0, this protocol would allow the two processors to swap 8K blocks of Dual-Port RAM with each other.

The blocks do not have to be any particular size and can even be variable, depending upon the complexity of the software using the semaphore flags. All eight semaphores could be used to divide the Dual-Port RAM or other shared resources into eight parts. Semaphores can even be assigned different meanings on different sides rather than being given a common meaning as was shown in the example above.

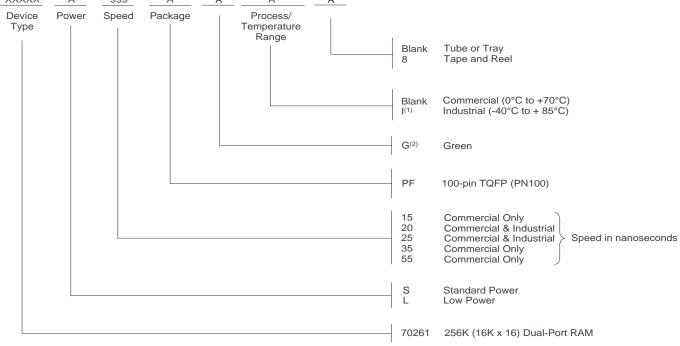
Semaphores are a useful form of arbitration in systems like disk interfaces where the CPU must be locked out of a section of memory during

a transfer and the I/O device cannot tolerate any wait states. With the use of semaphores, once the two devices has determined which memory area was "off-limits" to the CPU, both the CPU and the I/O devices could access their assigned portions of memory continuously without any wait states.

Semaphores are also useful in applications where no memory "WAIT" state is available on one or both sides. Once a semaphore handshake has been performed, both processors can access their assigned RAM segments at full speed.

Another application is in the area of complex data structures. In this case, block arbitration is very important. For this application one processor may be responsible for building and updating a data structure. The other processor then reads and interprets that data structure. If the interpreting processor reads an incomplete data structure, a major error condition may exist. Therefore, some sort of arbitration must be used between the two different processors. The building processor arbitrates for the block, locks it and then is able to go in and update the data structure. When the update is completed, the data structure block is released. This allows the interpreting processor to come back and read the complete data structure, thereby guaranteeing a consistent data structure.

## IDT70261S/L High-Speed 16K x 16 Dual-Port Static RAM with Interrupt Industrial and Commercial Temperature Ranges Ordering Information



3039 drw 19

NOTES:

1. Contact your local sales office for industrial temp range for other speeds, packages and powers.

- Green parts available. For specific speeds, packages and powers contact your local sales office.
- LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice PDN# SP-17-02

## Datasheet Document History

1/14/99:	Initiated datasheet document history
	Converted to new format
	Cosmetic and typographical corrections
	Pages 2 Added additional notes to pin configurations
6/4/99:	Changed drawing format
	Page 1 Corrected DSC number
2/18/00:	Added Industrial Temperature Ranges and removed related notes
	Replaced IDT logo
	Changed $\pm 200$ mV in table and waveform notes to 0 mV
5/22/00:	Page 3 Clarified TA parameter
	Page 4 Increased storage temperature parameter
	Page 5 DC Electrical parameters-changed wording from open to disabled

## Datasheet Document History (con't)

11/20/01:	Page 2 Added date revision for pin configuration
	Page 5 Removed Industrial temp for standard power 20ns speed from DC Electrical Characteristics
	Removed Industrial temp for low power 25ns speed from DC Electrical Characteristics
	Removed Industrial temp for standard and low power for 35ns & 55ns speeds from DC Electrical Characteristics
	Pages 6,8,11&13 Removed Industrial temp for 35ns and 55ns speeds from AC Electrical Characteristics
	Page 19 Removed Industrial temp from 35ns and 55ns in ordering information
01/29/09:	Page 19 Removed "IDT" from orderable part number
06/10/15:	Page 1 Added Green availability to Features
	Page 2 Removed IDT in reference to fabrication
	Page 2 & 19 The package code for PN100-1 changed to PN100 to match the standard package codes
	Page 19 Added Green and T&R indicators and the correlating footnotes to Ordering Information
06/28/18:	Product Discontinuation Notice - PDN# SP-17-02
	Last time buy expires June 15, 2018



*CORPORATE HEADQUARTERS* 6024 Silver Creek Valley Road San Jose, CA 95138 for SALES: 800-345-7015 or 408-284-8200 fax: 408-284-2775 www.idt.com *for Tech Support:* 408-284-2794 DualPortHelp@idt.com

The IDT logo is a registered trademark of Integrated Device Technology, Inc.

## **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

## IDT (Integrated Device Technology):

70261L20PFI870261L20PF70261S35PF870261S35PF870261S25PFI870261L25PF70261S15PF870261S25PFI70261S55PF870261L25PF870261S25PF870261L20PFGI870261S55PFG70261L15PFG870261L20PFI70261S55PF870261L55PF870261L20PF870261L15PFG70261L15PF70261L20PFGI70261S20PF70261S15PF70261L35PF870261L35PF870261L35PF870261L15PF70261L20PFGI70261S20PF70261S15PF70261L35PF870261L35PF870261L35PF8



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный) **Факс:** 8 (812) 320-02-42 **Электронная почта:** <u>org@eplast1.ru</u> **Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.